# Lecture 18 Amplificateurs à Transistor (I) Common-Source Amplifier

### **Outline**

- Amplifier fundamentals
- Common-source amplifier
- Common-source amplifier with current-source supply

## **Amplifier Fundamentals**

- Source resistance R<sub>S</sub> is associated *only* with small signal sources
- Choose  $I_D = I_{SUP} ---> DC$  output current

$$- I_{OUT} = 0$$
$$- V_{OUT} = 0$$



## 2. Common-Source Amplifier:



V-VSS

- Consider intrinsic voltage amplifier no loading
  - • $R_s = 0$ • $R_L ---> \infty$ •  $V_{GS} = V_{BIAS} - V_{SS}$
- $V_{BIAS}$ ,  $R_D$  and W/L of MOSFET selected to bias transistor in saturation and obtain desired output bias point (i.e.  $V_{OUT} = 0$ ).

Watch notation:  $v_{OUT}(t)=V_{OUT}+v_{out}(t)$ 

#### Load line view of amplifier:



#### Transfer characteristics of amplifier:



Want:

- Bias point calculation;
- Limits to signal swing
- Small-signal gain;
- Frequency response [in a few days]

**Bias point:** choice of  $V_{BIAS}$ , W/L, and  $R_D$  to keep transistor in saturation and to get proper quiescent  $V_{OUT}$ . Assume MOSFET is in saturation:

$$I_D = \frac{W}{2L} \mu_n C_{ox} \left( V_{BIAS} - V_{SS} - V_T \right)^2$$
$$I_R = \frac{V_{DD} - V_{OUT}}{R_D}$$

If we select  $V_{OUT}=0$ :

$$I_D = I_R = \frac{W}{2L} \mu_n C_{ox} \left( V_{BIAS} - V_{SS} - V_T \right)^2 = \frac{V_{DD}}{R_D}$$

Then:

$$V_{BIAS} = \sqrt{\frac{2I_D}{\frac{W}{L}\mu_n C_{ox}}} + V_{SS} + V_T$$

Equation that allows us to compute needed  $V_{\rm BIAS}$  given  $R_{\rm D}$  and W/L.



• Upswing: limited by MOSFET going into cut-off.

$$v_{out, \max} = V_{DD}$$

• Downswing: limited by MOSFET leaving saturation.

$$V_{DS,sat} = V_{GS} - V_T = \sqrt{\frac{2I_D}{\frac{W}{L} \mu_n C_{ox}}}$$

$$v_{out,\min} - V_{SS} = V_{BIAS} - V_{SS} - V_T = \sqrt{\frac{2I_D}{\frac{W}{L}\mu_n C_{ox}}}$$

Then:

or

$$v_{out,\min} = V_{BIAS} - V_T$$

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# **Generic view of the effect of loading on small-signal operation**

Two-port network view of small-signal equivalent circuit model of a voltage amplifier:

R<sub>in</sub> is *input resistance* R<sub>out</sub> is *output resistance* A<sub>vo</sub> is *unloaded voltage gain* 



**Small-signal voltage gain**  $A_{vo}$ **:** draw small-signal equivalent circuit model: Remove  $R_L$  and  $R_S$ 



# **Input Resistance**

- Calculation of input resistance, R<sub>in</sub>:
  - Load amplifier with R<sub>L</sub>
  - Apply test voltage (or current) at input, measure test current (or voltage).

For common-source amplifier:



No effect of loading at input.

# **Output Resistance**

- Calculation of output resistance, R<sub>out</sub>:
  - Load amplifier with R<sub>S</sub>
  - Apply test voltage (or current) at output, measure test current (or voltage).
  - Set input source equal zero

For common-source amplifier:





### **Current Source Supply**

I—V characteristics of current source:



#### Equivalent circuit models :



large-signal model



- $i_{SUP} = 0$  for  $v_{SUP} \le 0$
- $i_{SUP} = I_{SUP} + v_{SUP} / r_{oc} \text{ for } v_{SUP} > 0$
- High small-signal resistance r<sub>oc.</sub>







#### Use PMOS for current source supply



Bias point: Assume both transistors in saturation  $V_{OUT} = 0$ 

$$I_{SUP} = -I_{Dp} = \left(\frac{W}{2L}\right)_p \mu_p C_{ox} \left(V_{DD} - V_B + V_{Tp}\right)^2$$

$$I_{SUP} = I_{Dn} = \left(\frac{W}{2L}\right)_n \mu_n C_{ox} \left(V_{BIAS} - V_{SS} - V_{Tn}\right)^2$$

$$V_{BIAS} = \sqrt{\frac{2I_{SUP}}{\left(\frac{W}{L}\right)_n \mu_n C_{ox}}} + V_{SS} + V_T$$



• Upswing: limited by PMOS leaving saturation.

$$V_{SD,sat} = V_{SG} + V_{Tp} = \sqrt{\frac{2I_{SUP}}{\left(\frac{W}{L}\right)_p}\mu_p C_{ox}}$$

 $V_{DD} - v_{out,max} = V_{DD} - V_B + V_{Tp}$  $v_{out,max} = V_B - V_{Tp}$ 

- Downswing: limited by NMOS leaving saturation.
- Same result as with resistive supply current.

$$v_{out,\min} = V_{BIAS} - V_T$$

#### 3. Common-source amplifier with currentsource supply (contd.)

Current source characterized by high output resistance:  $r_{oc}$ . Significantly higher than amplifier with resistive supply.



- Voltage gain:  $A_{vo} = -g_m (r_o //r_{oc})$ .
- Input resistance :  $R_{in} = \infty$
- Output resistance:  $R_{out} = r_o / / r_{oc}$ .

# **Relationship between circuit figures of merit and device parameters**

Remember:

$$g_m = \sqrt{2I_D \frac{W}{L} \mu_n C_{ox}}$$
$$r_o \approx \frac{1}{\lambda_n I_D} \propto \frac{L}{I_D}$$

Then:

	Circuit Parameters		
	A <sub>vo</sub>	R <sub>in</sub>	R <sub>out</sub>
Device*	$g_{m}(r_{o}//r_{oc})$	$\infty$	$r_o //r_{oc}$
Parameters	811(-000)		-000
$I_{SUP}$ $\uparrow$	$\downarrow$	_	$\downarrow$
w↑	$\uparrow$	-	-
$\mu_n C_{ox} \uparrow$	$\uparrow$	-	-
L 1	$\uparrow$	-	$\uparrow$

 $\ast$  adjustments are made to  $V_{\rm BIAS}$  so that none of the other parameters change

CS amplifier with current source supply is a good voltage amplifier ( $R_{in}$  high and  $|A_{vo}|$  high), but  $R_{out}$  high too  $\Rightarrow$  voltage gain degraded if  $R_L \ll r_o//r_{oc}$ .

## What did we learn today?

#### Summary of Key Concepts for CS amplifier

- Bias Calculations
- Signal Swing
- Small Signal Circuit Parameters
  - Voltage Gain  $A_{VO}$
  - Transconductance G<sub>m</sub>
  - Input Resistance R<sub>in</sub>
  - Output Resistance R<sub>out</sub>
- Relationship between small signal circuit and device parameters